TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

FEATURES

Power dissipation

P_{CM} : 0.2W (Tamb=25°C)

Collector current

I_{CM} : -0.8A

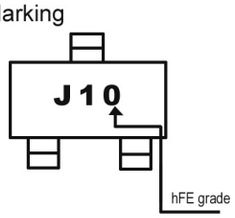
Collector-base Voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

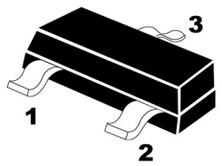
T_J, T_{stg} : -55°C to +150°C

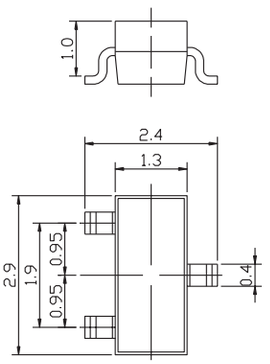
Marking



SOT-23

1. BASE
2. EMITTER
3. COLLECTOR





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0		-30	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0		-100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	100	320	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-800mA	40		
Collector-emitter saturation voltage	V_{CEsat}	I_C=-500mA, I_B=-20mA		-0.4	V

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320